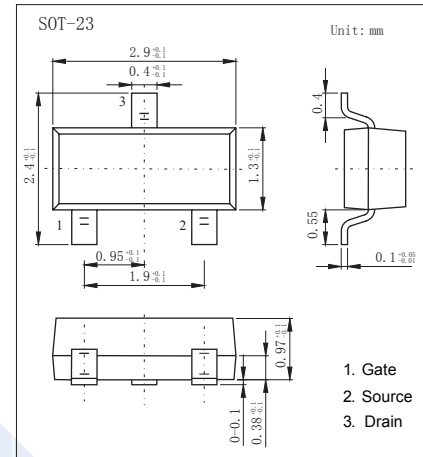


P-Channel MOSFET

KO3415A

■ Features

- V_{DS} (V) = -12V
- I_D = -4.1 A (V_{GS} = -4.5V)
- $R_{DS(ON)}$ < 45m Ω (V_{GS} = -4.5V)
- $R_{DS(ON)}$ < 60m Ω (V_{GS} = -2.5V)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	-4.1	A
Pulsed Drain Current	I_{DM}	-30	
Power Dissipation	P_D	1.2	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{BSS}	$I_D = -250 \mu\text{A}$, $V_{GS} = 0\text{V}$	-12			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12\text{V}$, $V_{GS} = 0\text{V}$			-1	μA
		$V_{DS} = -12\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 55^\circ\text{C}$			-5	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 12\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-0.45		-1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{V}$, $I_D = -4.1\text{A}$			45	m Ω
		$V_{GS} = -2.5\text{V}$, $I_D = -3\text{A}$			60	
Diode Forward Voltage	V_{SD}	$I_S = -1\text{A}$, $V_{GS} = 0\text{V}$			-1	V

■ Marking

Marking	3415A
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